

Silicon PNP Power Transistors

2SB979

DESCRIPTION

With TO-3PN package
 ·Wide area of safe operation

APPLICATIONS

·For power amplifier and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

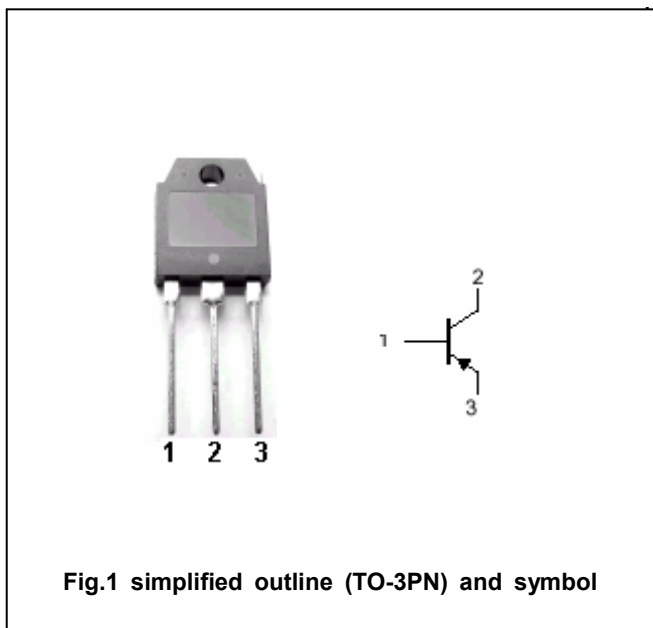


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
P_C	Collector power dissipation	$T_C=25^\circ C$	60	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-30mA ; I _B =0	-100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-5mA ; I _E =0	-100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-1.5	V
V _{BE}	Base-emitter on voltage	I _C =-1A; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-50	μA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-5V	40		200	
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-5V	20			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V	20			MHz

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PACKAGE OUTLINE

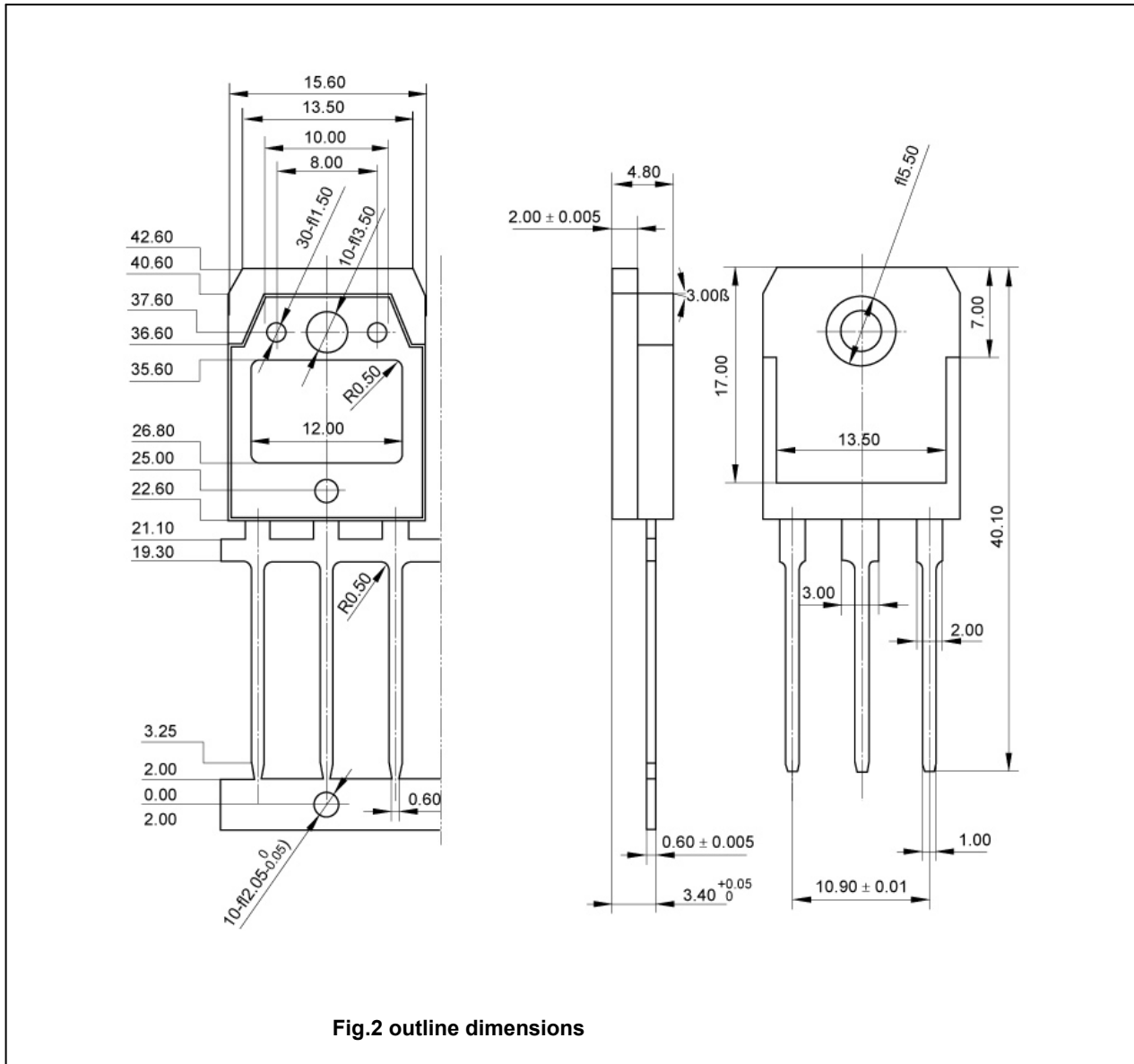


Fig.2 outline dimensions